

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25$; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

ELECTRICAL CHARACTERISTICS ($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	35	mA
V_{GT}		- -	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	70	mA
				80	
I_H	$I_T=500mA$		MAX.	60	mA
dV/dt	$V_D=800V$ Gate Open $T_j=125$		MIN.	1000	V/ μs
(dI/dt)c	(dV/dt)c=20V/ μs $T_j=125$		MIN.	15	A/ms
t_{on}	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	7	μs
t_{off}				50	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=42A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.73	V
R_D	Dynamic resistance	$T_j=125$	25	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	μA
I_{RRM}		$T_j=125$	4	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

FIG.1: Maximum power dissipation

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



